

09/974, 814

	Type	Hits	Search Text	DBs
1	IS&R	0	("standby adj current").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	2561	standby adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	8	(standby adj current) same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	195	(standby adj current) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	187	((standby adj current) and silicide) not ((standby adj current) same silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	52	((standby adj current) and silicide) not ((standby adj current) same silicide)) and (sputter or sputtering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1003	argon adj (sputter or sputtering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	17	(argon adj (sputter or sputtering)) near5 (nanometer or nm or angstrom)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	0	quach/\$.xp.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	1171	quach.xp.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	383	quach.xp. and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	4024	battery adj driven	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	19	((battery adj driven) and (mos or fet or mosfet)) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	111	battery same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	367	(battery adj driven) and (mos or fet or mosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	20	(battery adj driven) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	6436	battery adj (driven or operating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
1	2003/06/13 09:50			0
2	2003/06/13 09:50			0
3	2003/06/13 10:52			0
4	2003/06/13 10:03			0
5	2003/06/13 09:59			0
6	2003/06/13 09:59			0
7	2003/06/13 10:03			0
8	2003/06/13 10:05			0
9	2003/06/13 10:05			0
10	2003/06/13 10:06			0
11	2003/06/13 10:26			0
12	2003/06/13 10:35			0
13	2003/06/13 10:29			0
14	2003/06/13 10:33			0
15	2003/06/13 10:34			0
16	2003/06/13 10:35			0
17	2003/06/13 10:36			0

	Type	Hits	Search Text	DBs
18	BRS	968	(battery adj (driven or operating)) and (MOS or MOSFET or FET or MIS or MISFET or CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	27	((battery adj (driven or operating)) and (MOS or MOSFET or FET or MIS or MISFET or CMOS)) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	10641	gate adj length	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	89	subquarter adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	7	(gate adj length) and (subquarter adj micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	14	(subquarter adj micron) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	780	sub adj quarter adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	202	(sub adj quarter adj micron) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	40	((sub adj quarter adj micron) same gate) same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
18	2003/06/13 10:38			0
19	2003/06/13 10:38			0
20	2003/06/13 10:52			0
21	2003/06/13 10:54			0
22	2003/06/13 10:53			0
23	2003/06/13 10:56			0
24	2003/06/13 10:56			0
25	2003/06/13 10:56			0
26	2003/06/13 14:13			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	IS&R	L1	2	("5344793").PN.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/1 3 14:31	
2	BRS	L2	3487	ohm adj square	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/1 3 14:32	
3	BRS	L3	2880	cosi or (cobalt adj silicide)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/1 3 14:32	
4	BRS	L4	1	2 near3 3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/1 3 14:34	

	Error Definition	Er ro rs
1		0
2		0
3		0
4		0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	15	2 same 3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/06/1 3 14:34	

	Error Definition	Er ro rs
5		0